

Silicon PNP Power Transistors

2SA633

DESCRIPTION

- With TO-202 package
- High current capability

APPLICATIONS

- Power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

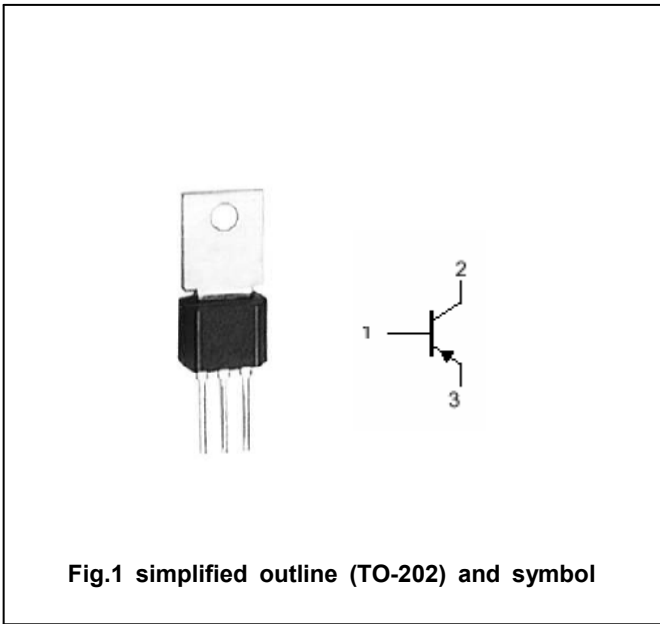


Fig.1 simplified outline (TO-202) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-30	V
V _{CEO}	Collector-emitter voltage	Open base	-30	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-2	A
I _{CM}	Collector current-peak		-3	A
I _B	Base current		-0.6	A
P _C	Collector power dissipation	T _c =25°C	10	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA; I _B =0	-30			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-0.1mA; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1.5A; I _B =-0.15A			-1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-2A; I _B =-0.2 A			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-20V; I _E =0			-1	μA
I _{CEO}	Collector cut-off current	V _{CE} =-12V; I _B =0			-100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-3V; I _C =0			-1	μA
h _{FE-1}	DC current gain	I _C =-20mA; V _{CE} =-5V	20			
h _{FE-2}	DC current gain	I _C =-1A; V _{CE} =-5V	80		250	
f _T	Transition frequency	I _C =-0.1A; V _{CE} =-5V		60		MHz

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PACKAGE OUTLINE

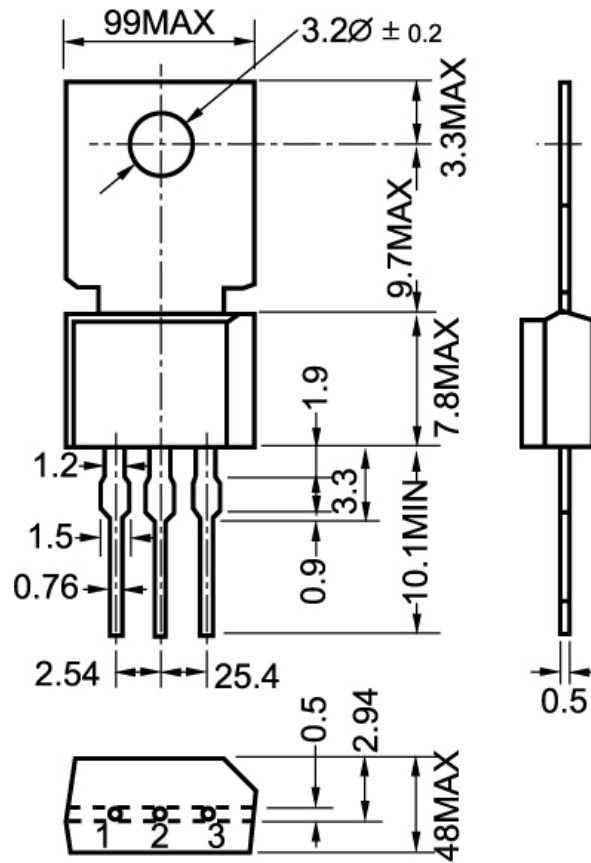


Fig.2 outline dimensions